



#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max
001/	$35m\Omega$ @ $V_{GS} = 10V$	4.6A
20V	40mΩ @ V <sub>GS</sub> = 4.5V	4.3A

## **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

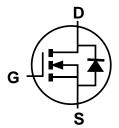
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

#### **Mechanical Data**

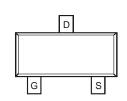
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



Top View

nai Schematic

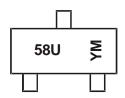
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN2058U-7	SOT23	3,000/Tape & Reel
DMN2058U-13	SOT23	10.000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

## **Marking Information**



 $58U = Product Type Marking Code YM = Date Code Marking Y or <math>\overline{Y} = Year (ex: D = 2016)$  M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022	!	2023
Code	D		Е	F		G	Н		ı	J		K
Month	Jan	Feb	Mar	Apr	Ma	y Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMN2058U

Document number: DS38468 Rev. 1 - 2



# **Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	20	V		
Gate-Source Voltage	$V_{GSS}$	±12	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	4.6 3.7	А
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	1.2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	24	А		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		$P_{D}$	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	172	°C/W
Power Dissipation (Note 6)		P <sub>D</sub>	1.13	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	111	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

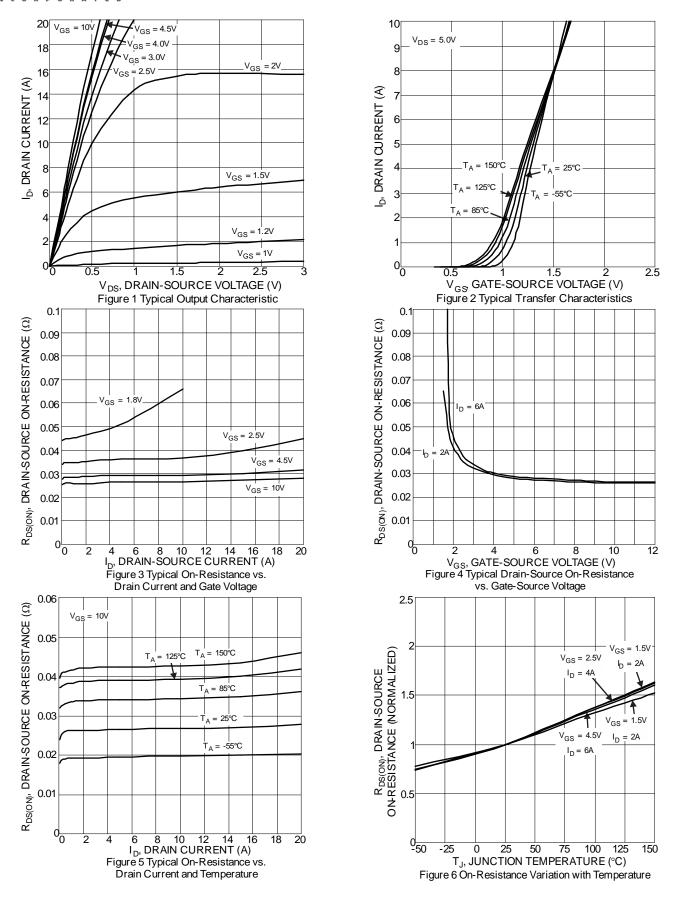
## Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	0.6	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
			27	35		$V_{GS} = 10V, I_D = 6.0A$		
Static Drain-Source On-Resistance			30	40	mΩ	$V_{GS} = 4.5V, I_D = 5.0A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	37	60	11122	$V_{GS} = 2.5V, I_D = 4.0A$		
		_	49	91		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 2.0A		
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C <sub>ISS</sub>		281	_		101/11/		
Output Capacitance	Coss		50	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	39	_		1 = 1.000112		
Gate Resistance	R <sub>G</sub>	_	3.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	3.6	_				
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	7.7	_		V 40V I 0.0A		
Gate-Source Charge	Q <sub>GS</sub>	_	0.5	_	nC	$V_{DS} = 10V, I_{D} = 6.0A$		
Gate-Drain Charge	$Q_{GD}$	_	0.9	_				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.0	_				
Turn-On Rise Time	t <sub>R</sub>	_	4.9	_		$V_{GS} = 4.5V$ , $V_{DD} = 10V$ , $R_{G} = 6\Omega$ ,		
Turn-Off Delay Time	t <sub>D(OFF)</sub>		9.9	_	ns	$I_D = 6.0A$		
Turn-Off Fall Time	t <sub>F</sub>		3.3	_	1			
Body Diode Reverse Recovery Time	t <sub>RR</sub>		5.4	_	ns	$I_F = 6.0A$ , $di/dt = 100A/\mu s$		
Body Diode Reverse Recovery Charge	$Q_{RR}$		0.7	_	nC	$I_F = 6.0A$ , di/dt = 100A/ $\mu$ s		

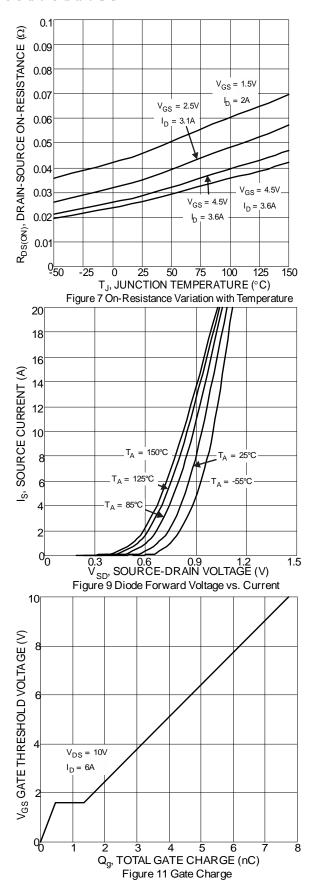
Notes:

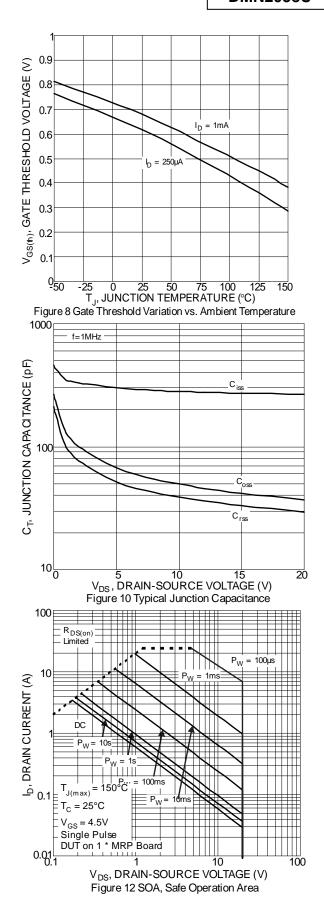
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



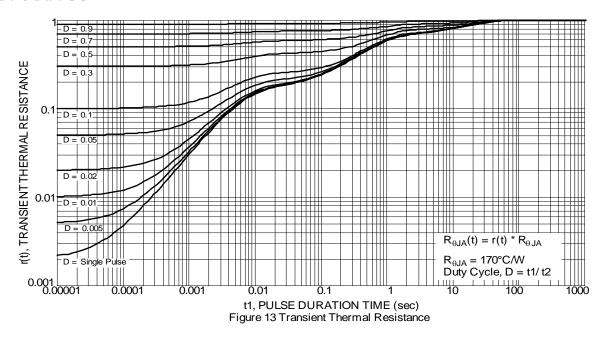










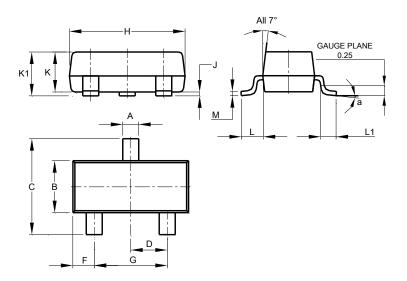




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

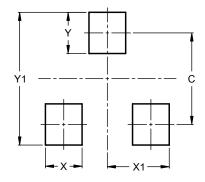


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
Y1	29				



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